

Product Summary

V(BR)DSS	RDS(on)MAX	ID
60V	5Ω@10V	340mA
	5.3Ω@4.5V	

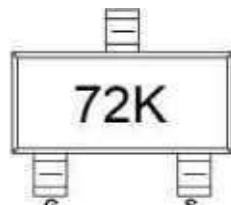
Feature

- High density cell design for Low Ros(on)
- Voltage controlled small signal switch
- Rugged and reliable
- ESD protected Gate HBM 2.5KV

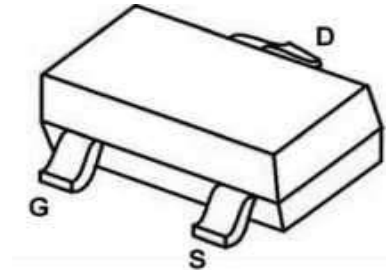
Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

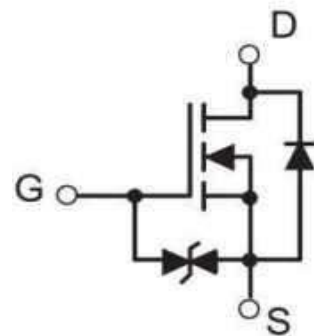
MARKING:



SOT-23



Schematic diagram



ABSOLUTE MAXIMUM RATINGS (T_a=25° C unless otherwise noted)

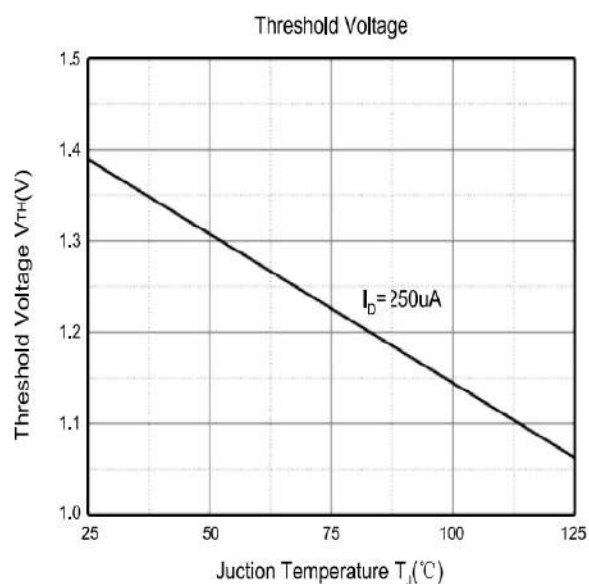
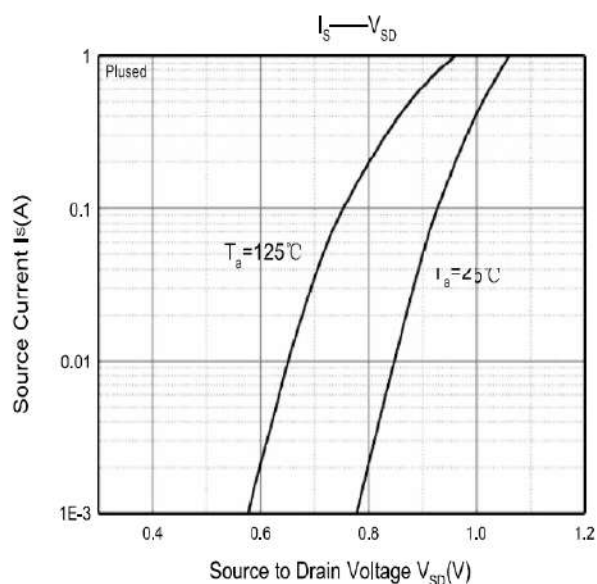
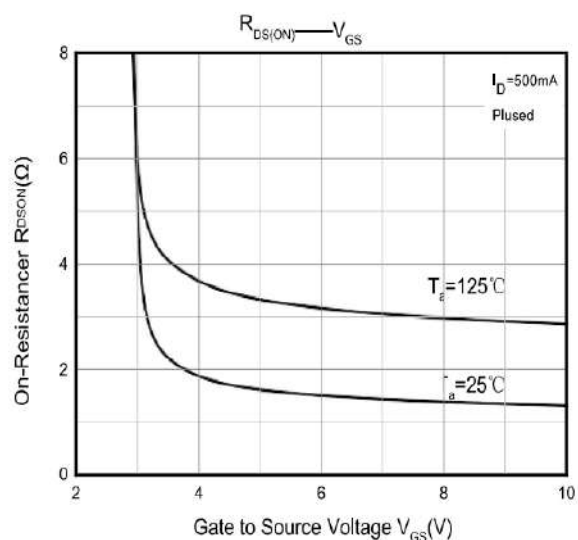
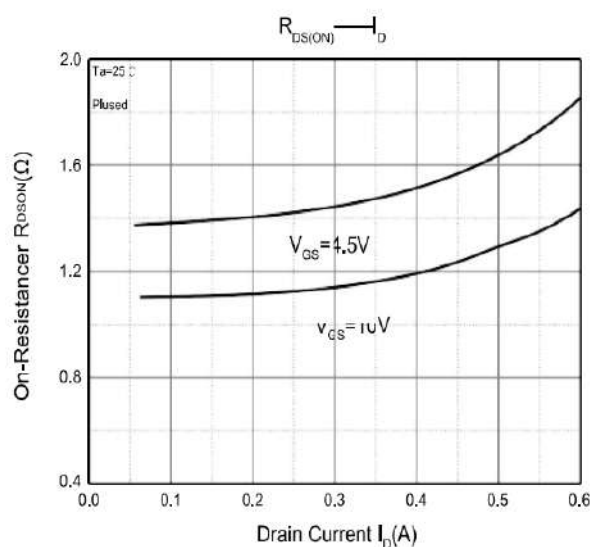
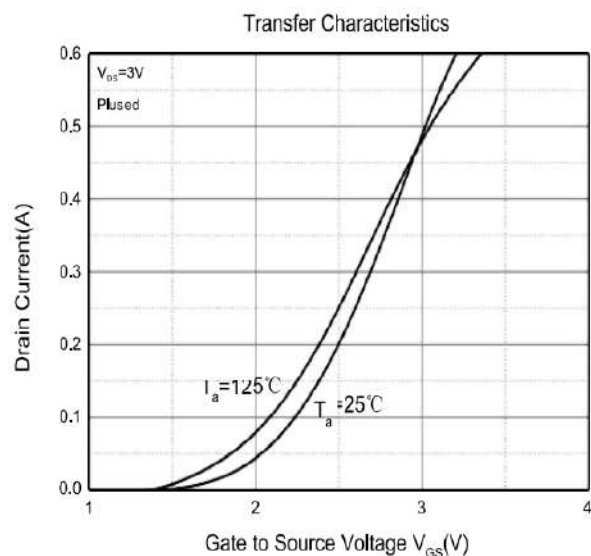
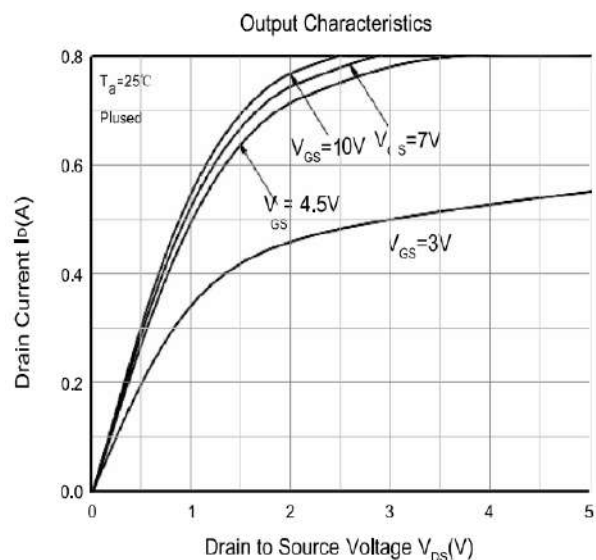
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	+20	V
Continuous Drain Current	I _D	340	mA
Power Dissipation	P _D	0.35	W
Thermal Resistance from Junction to Ambient	R _{BJA}	357	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55+150	°C

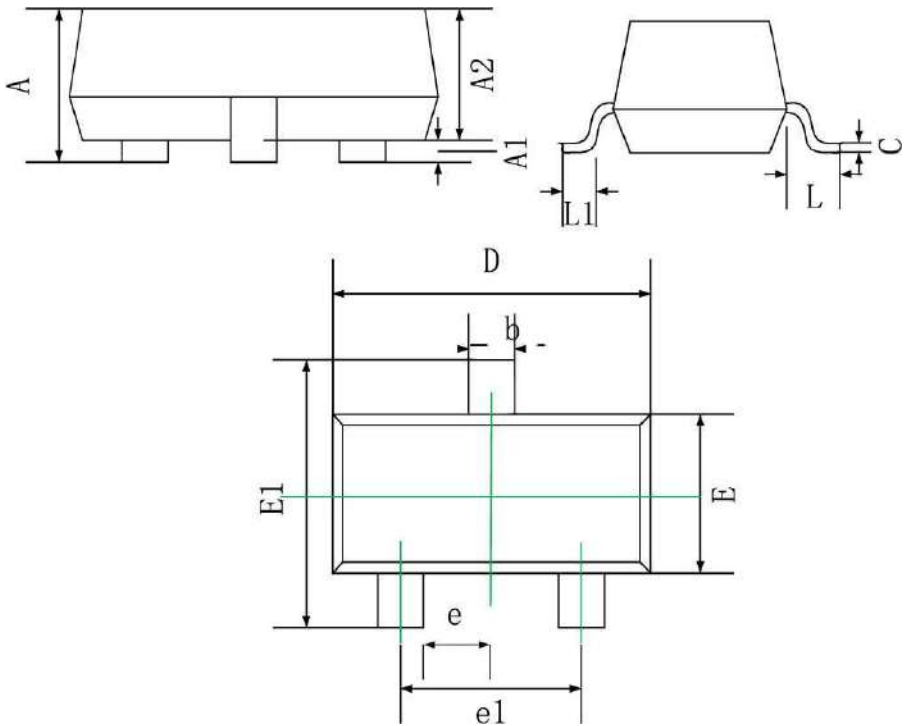
MOSFET ELECTRICAL CHARACTERISTICS (T_a=25° C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250pA	60			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =48V, V _{GS} =0V			1	uA
Gate-body leakage current	I _{GSSI}	V _{GS} =±20V, V _{DS} = 0V			±10	MA
	I _{GSS2}	V _{GS} =±10V, V _{DS} = 0V			±200	nA
	I _{GSS2}	V _{GS} =±5V, V _{DS} =0V			±100	nA
Gate threshold voltage*	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250 A	1	1.4	2.5	V
Drain-source on-resistance*	R _{DS(on)}	V _{GS} =10V, I _D =500mA		1.3	5	Q
		V _{GS} =4.5V, I _D =200mA		1.4	5.3	
Recovered charge	Q _r	V _{GS} =0V, I _s =300mA, V _R =25V, dI _s /dt=-100A/pS		30		nC
Dynamic characteristics**						
Input Capacitance	C _{iss}	V _D S=10V, V _G S=0V, f=1MHz			40	pF
Output Capacitance	C _{oss}				30	
Reverse Transfer Capacitance	C _{rss}				10	
Switching Characteristics**						
Turn-on delay time	t _{d(on)}	V _{GS} =10V, V _D D=50V, R _G =50Q			10	ns
Turn-off delay time	t _{d(off)}	R _G S=50Q, R _L =250Q			15	
Reverse recovery Time	t _{rr}	V _{GS} =0V, I _s =300mA, V _R =25V, dI _s /d _t =-100A/pS		30		
Source-Drain Diode characteristics						
Diode Forward voltage	V _{sD}	V _{GS} =0V, I _s =300mA		0.97	1.5	V
GATE-SOURCE ZENER DIODE						
Gate-Source Breakdown Voltage	BV _{GSO}	I _{GS} =±1mA(Open Drain)	±21.5		±30	V

Notes:

*Pulse Test: Pulse Width <300ps, Duty Cycle <2%. **These parameters have no way to verify.

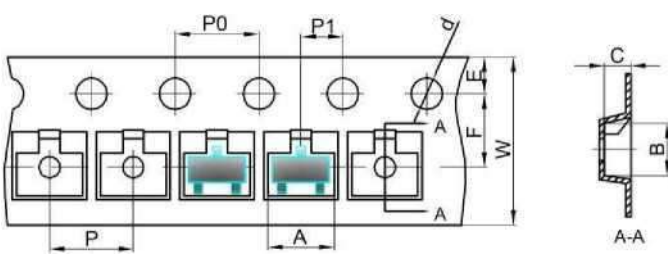




Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50

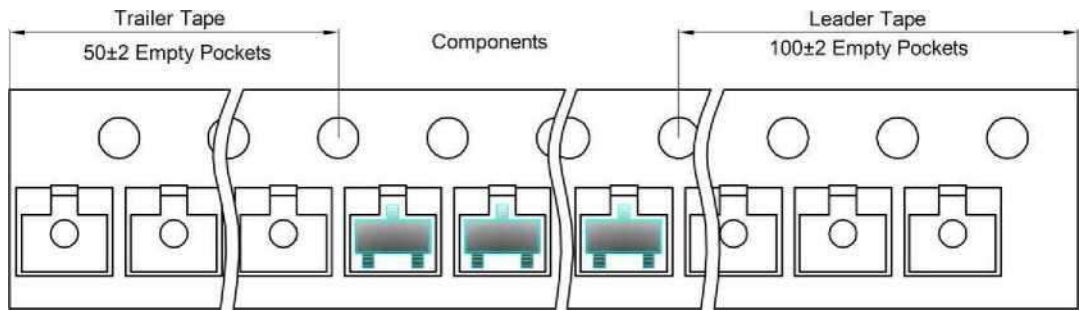
SOT-23 Tape and reel

SOT-23 Embossed Carrier Tape

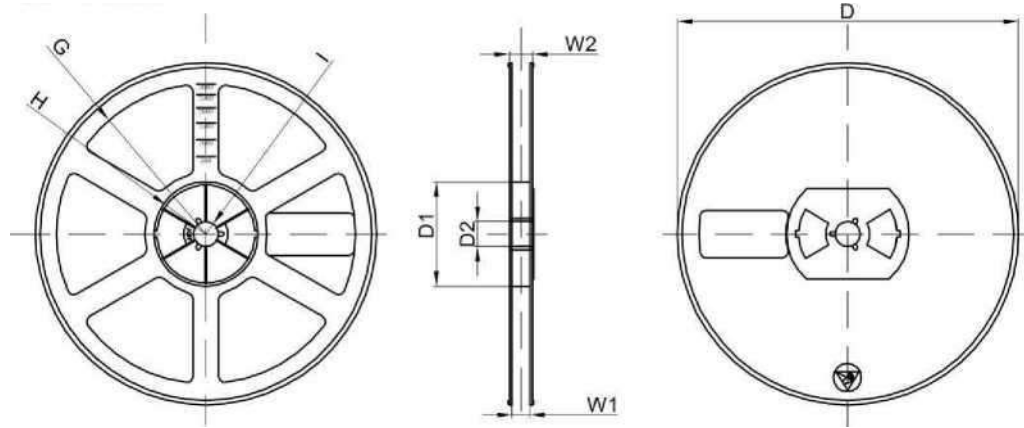


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	PO	P	P1	w
SOP23	3.15	2.77	1.22	01.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23 Tape Leader and Trailer



SOT-23 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7"Dia	0178.00	54.40	13.00	R78.00	R25.60	R6.50	9,50	12,30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203x203*195	120,000 pcs	438x438x220	